



First Named Inventor	Leonard Forbes	INFORMATION DISCLOSURE STATEMENT FORM PTO-1449
Serial No.	10/775,424	
Filing Date	February 10, 2004	
Group Art Unit	2655	
Examiner Name	Unknown	
Confirmation No.	9726	
Attorney Docket No.	400.270US01	
Title: NROM FLASH MEMORY CELL WITH INTEGRATED DRAM		Sheet 1 of 7

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